

• General Description

The ZMS075N10S combines advanced trench MOSFET technology with a low resistance package to provide extremely low $R_{DS(ON)}$.

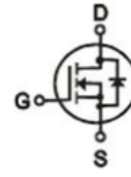
• Features

- Advance device constructure
- Low $R_{DS(ON)}$ to minimize conduction loss
- Low Gate Charge for fast switching
- Low Thermal resistance

• Application

- Synchronous Rectification for AC-DC/DC-DC converter
- Oring switches
- Power Tools

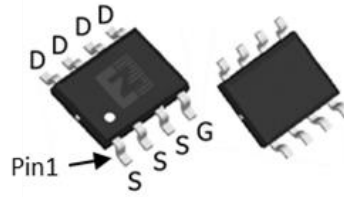
• Product Summary



$$V_{DS} = 100V$$

$$R_{DS(ON)} = 7.5m\Omega$$

$$I_D = 15A$$



SOP8

• Ordering Information:

Part NO.	ZMS075N10S
Marking	ZMS075N10
Packing Information	REEL TAPE
Basic ordering unit (pcs)	4000

• Absolute Maximum Ratings ($T_C = 25^\circ C$)

Parameter	Symbol	Rating	Unit
Drain-Source Voltage	V_{DS}	100	V
Gate-Source Voltage	V_{GS}	± 20	V
Continuous Drain Current	$I_{D@TC=25^\circ C}$	15	A
	$I_{D@TC=75^\circ C}$	11.4	A
	$I_{D@TC=100^\circ C}$	9.4	A
Pulsed Drain Current ^①	I_{DM}	32	A
Total Power Dissipation($TC=25^\circ C$)	$P_D@TC=25^\circ C$	3.6	W
Total Power Dissipation($TA=25^\circ C$)	$P_D@TA=25^\circ C$	0.69	W
Operating Junction Temperature	T_J	-55 to 150	$^\circ C$
Storage Temperature	T_{STG}	-55 to 150	$^\circ C$
Single Pulse Avalanche Energy	E_{AS}	50	mJ

•Thermal resistance

Parameter	Symbol	Min.	Typ.	Max.	Unit
Thermal resistance, junction - case	R_{thJC}	-	-	34	° C/W
Thermal resistance, junction - ambient	R_{thJA}	-	-	180	° C/W
Soldering temperature, wavesoldering for 10s	T_{sold}	-	-	265	° C

•Electronic Characteristics

Parameter	Symbol	Condition	Min.	Typ	Max.	Unit
Drain-Source Breakdown Voltage	BV_{DSS}	$V_{GS} = 0V, I_D = 250\mu A$	100			V
Gate Threshold Voltage	$V_{GS(TH)}$	$V_{GS} = V_{DS}, I_D = 250\mu A$	1.6		2.5	V
Drain-Source Leakage Current	I_{DSS}	$V_{DS} = 100V, V_{GS} = 0V$			1.0	μA
Gate- Source Leakage Current	I_{GSS}	$V_{GS} = \pm 20V, V_{DS} = 0V$			± 100	nA
Static Drain-source On Resistance	$R_{DS(ON)}$	$V_{GS} = 10V, I_D = 15A$		7.5	9.5	m Ω
		$V_{GS} = 4.5V, I_D = 10A$		9.5	11.5	m Ω
Forward Transconductance	g_{FS}	$V_{DS} = 25V, I_D = 10A$		16		S
Diode Forward Voltage	V_{FSD}	$I_S = 15A$			1.2	V

•Electronic Characteristics

Parameter	Symbol	Condition	Min.	Typ	Max.	Unit
Input capacitance	C_{iss}	$V_{GS} = 0V, V_{DS} = 25V$ $f = 1MHz$	-	2120	-	pF
Output capacitance	C_{oss}		-	940	-	
Reverse transfer capacitance	C_{rss}		-	48	-	

•Switching Parameters($T_a = 25^\circ C$)

Parameter	Symbol	Condition	Min.	Typ	Max.	Unit
Total gate charge	Q_g	$V_{DD} = 25V$	-	28	-	nC
Gate - Source charge	Q_{gs}	$I_D = 8A$	-	5.5	-	
Gate - Drain charge	Q_{gd}	$V_{GS} = 10V$	-	5.3	-	
Body Diode Reverse Recovery Time	t_{rr}	$I_F = 15A,$ $di/dt = 100A/\mu s$		47		nS
Body Diode Reverse Recovery Charge	Q_{rr}	$I_F = 15A,$ $di/dt = 100A/\mu s$		38		nC

Note: ① Pulse Test : Pulse width $\leq 300\mu s$, Duty cycle $\leq 2\%$;

Fig.1 Gate-Charge Characteristics

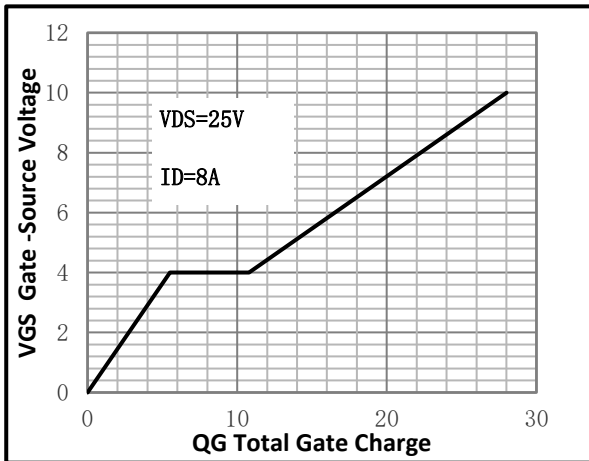


Fig.2 Capacitance Characteristics

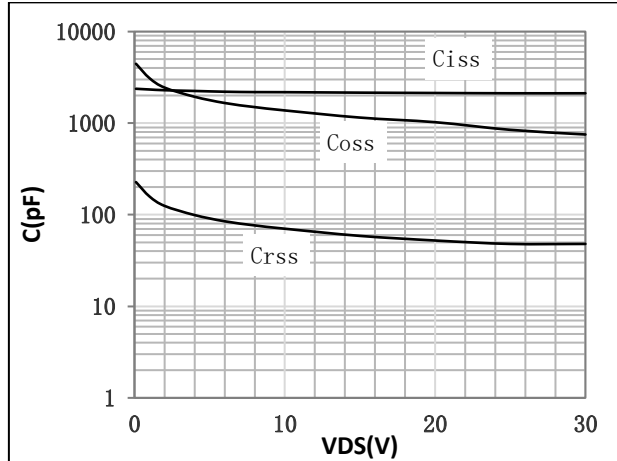


Fig.3 Power Dissipation

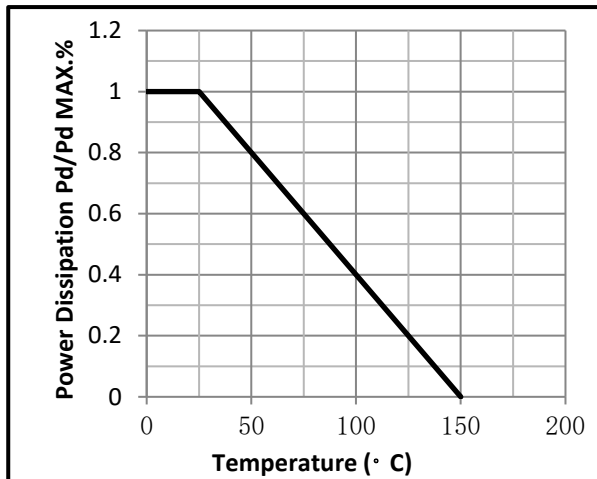


Fig.4 Typical output Characteristics

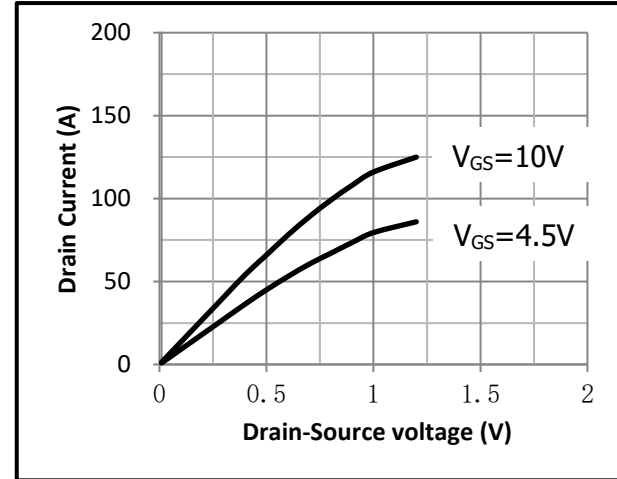


Fig.5 Threshold Voltage V.S Junction Temperature

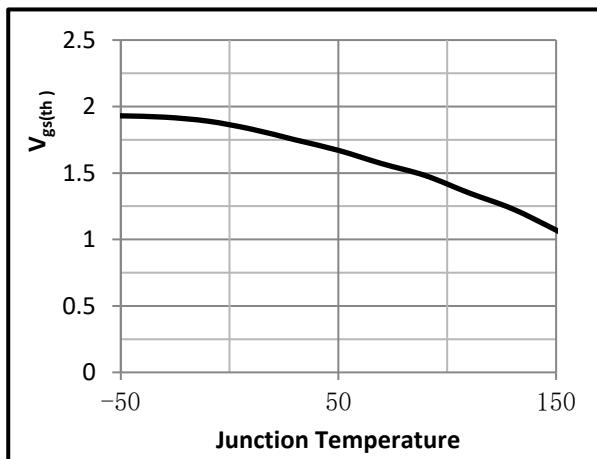


Fig.6 Resistance V.S Drain Current

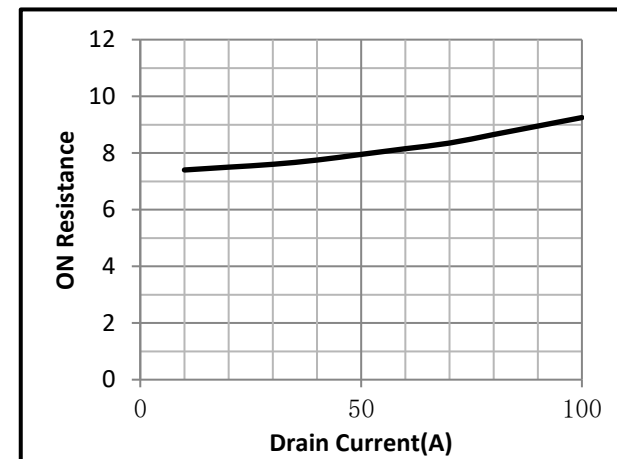


Fig.7 On-Resistance VS Gate Source Voltage

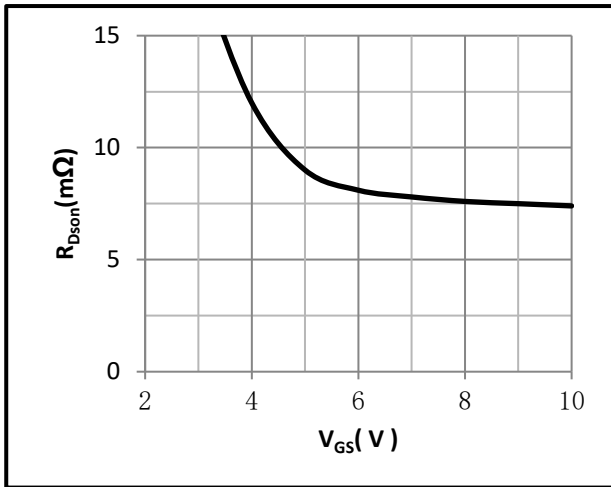


Fig.8 On-Resistance V.S Junction Temperature

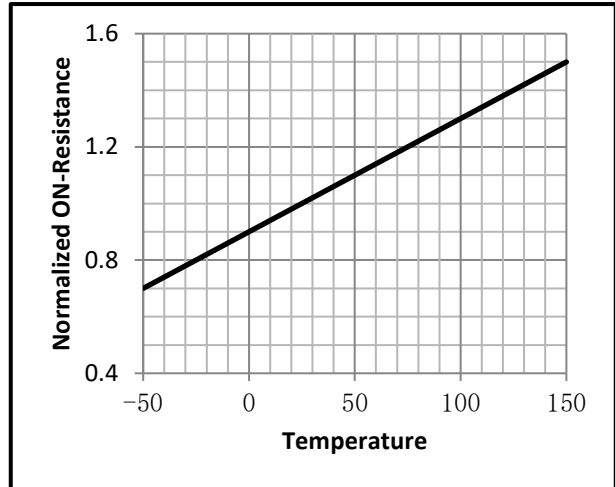


Fig.9 Gate Charge Measurement Circuit

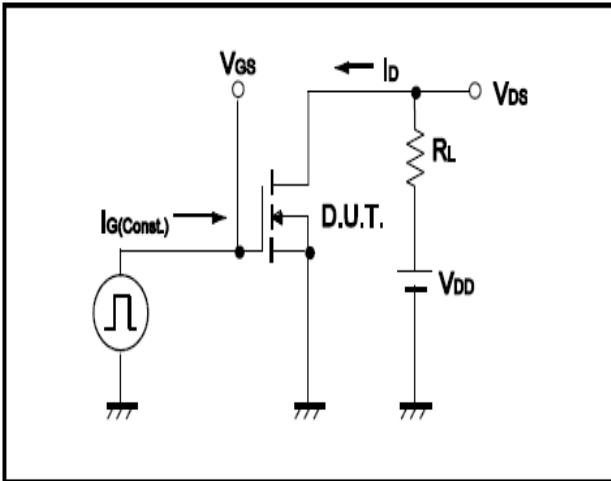


Fig.10 Gate Charge Waveform

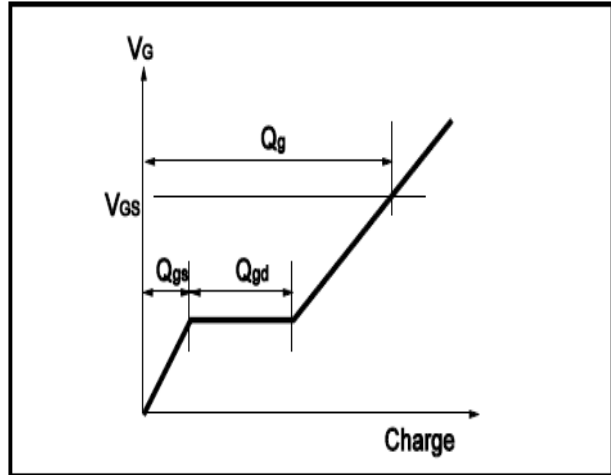


Fig.11 Switching Time Measurement Circuit

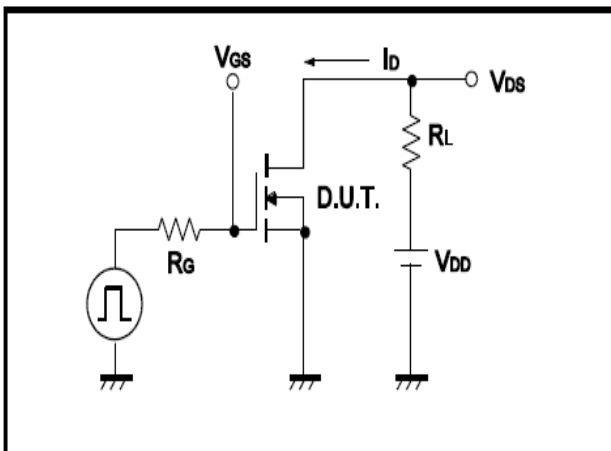
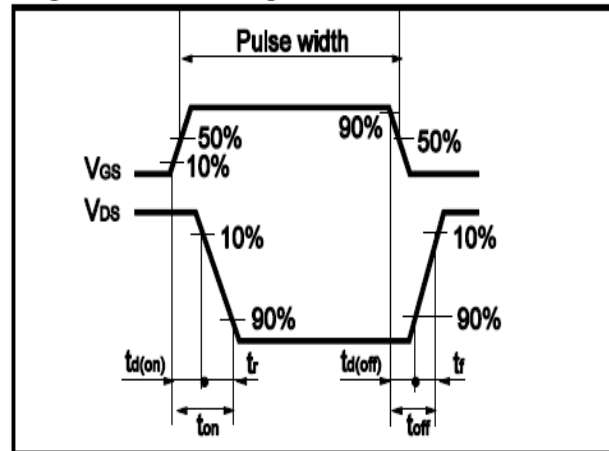


Fig.12 Switching Time Waveform



•**Dimensions(SOP8)**

Unit: mm

SYMBOL	min	TYP	max	SYMBOL	min		max
A	4.80		5.25	C	1.30		1.75
A1	0.37		0.49	C1	0.55		0.75
A2		1.27		C2	0.55		0.65
A3		0.41		C3	0.05		0.20
B	5.80		6.20	C4	0.10	0.20	0.23
B1	3.80		4.00	D		1.05	
B2		5.00		D1	0.40		0.62

